

Customer No.: 31561  
Docket No.: 9246-US-PA  
Application No.: 10/604,650

**In The Claims**

1. (original) A substrate, comprising:  
a dielectric structure;  
an interconnection structure interlacing inside the dielectric structure; and  
a solder mask covering the dielectric structure, wherein the solder mask has a coefficient of thermal expansion substantially equal to the dielectric structure contacting the solder mask.
2. (original) The substrate according to claim 1, wherein the material of the solder mask is epoxy resin.
3. (original) The substrate according to claim 1, wherein the material of the solder mask is bismaleimide-triazine.
4. (original) The substrate according to claim 1, wherein the solder mask further covers the interconnection structure, the solder mask having at least one opening to expose the interconnection structure.
5. (original) The substrate according to claim 1, wherein the solder mask has the same material as the dielectric structure contacting the solder mask.
6. (currently amended) A substrate, comprising:  
a dielectric structure;  
an interconnection structure interlacing inside the dielectric structure; and  
a solder mask covering the dielectric structure, wherein the glass transition temperature of the material used for manufacturing the solder mask is over 200 degree C. [[w]]

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7. (original) The substrate according to claim 6, wherein the solder mask further covers the interconnection structure, the solder mask having at least one opening to expose the interconnection structure.

8. (original) The substrate according to claim 6, wherein the material of the solder mask is epoxy resin.

9. (original) The substrate according to claim 6, wherein the material of the solder mask is bismaleimide-triazine.

10-25 (cancelled)

26. (new) The substrate according to claim 1, wherein the dielectric structure includes a first dielectric layer and two second dielectric layers on both sides of the dielectric layer, wherein a portion of the interconnection structure is disposed between the first dielectric layer and the second dielectric layer.

27. (new) The substrate according to claim 5, wherein the dielectric structure includes a first dielectric layer and two second dielectric layers on both sides of the dielectric layer, wherein a portion of the interconnection structure is disposed between the first dielectric layer and the second dielectric layer.